Features

- Very Low FOM $R_{DS(on)} \times Q_g$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 1
- Halogen Free Available Upon Request By Adding Suffix "-HF"
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-CHANNEL Super-Junction Power MOSFET

Maximum Ratings

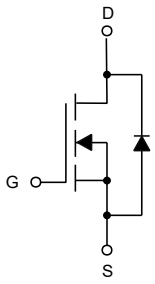
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 62°C/W Junction to Ambient
- Thermal Resistance: 2°C/W Junction to Case

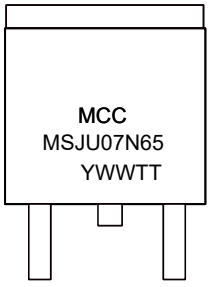
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Volltage		V_{GS}	±30	V
Continuous Drain Current	T_C=25°C	I_D	7	A
	T_C=100°C		4.2	
Pulsed Drain Current (Note 1)		I_{DM}	21	A
Single Pulse Avalanche Energy (Note 2)		E_{AS}	142	mJ
Avalanche Current		I_{AR}	1.3	A
Repetitive Avalanche Energy		E_{AR}	0.21	mJ
Total Power Dissipation	T_C=25°C	P_D	63	W

Note:

1. Repetitive Rating; Pulse Width Limited by Maximum Junction Temperature.
2. I_{AS}=2.4A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C.

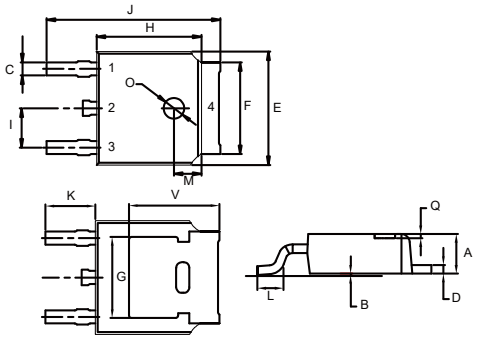
Internal Structure and Marking Code





YWWTT: 5 codes in total
Y is the year
WW is the cycle
TT is the line type

DPAK(TO-252)



1. Gate
2,4. Drain
3. Source

DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.087	0.094	2.20	2.40	
B	0.000	0.005	0.00	0.13	
C	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
H	0.236	0.244	6.00	6.20	
I	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
O	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	650			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±30V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=650V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2.5		4	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=3.5A		0.53	0.6	Ω
Gate Resistance	R_G	f = 1.0MHz Open Drain		19		Ω
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=3.5A		0.9	1.2	V
Continuous Body Diode Current	I_S				7	A
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=100V,V_{GS}=0V,f=1MHz		509		pF
Output Capacitance	C_{oss}			23		
Reverse Transfer Capacitance	C_{rss}			1.5		
Total Gate Charge	Q_g	V_{DD}=520V,V_{GS}=10V,I_D=7A		13		nC
Gate-Source Charge	Q_{gs}			2.8		
Gate-Drain Charge	Q_{gd}			5.6		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=400V, I_D=7A, R_G=25Ω		55		ns
Turn-On Rise Time	t_r			61		
Turn-Off Delay Time	$t_{d(off)}$			117		
Turn-Off Fall Time	t_f			42		
Reverse Recovery Time	t_{rr}	V_R=400V, I_F=7A, di_F/dt = 100A/μs		321		ns
Reverse Recovery Charge	Q_{rr}			3.4		μC
Peak Reverse Recovery Current	I_{rrm}			21.2		A

Curve Characteristics

Fig. 1 - Typical Output Characteristics

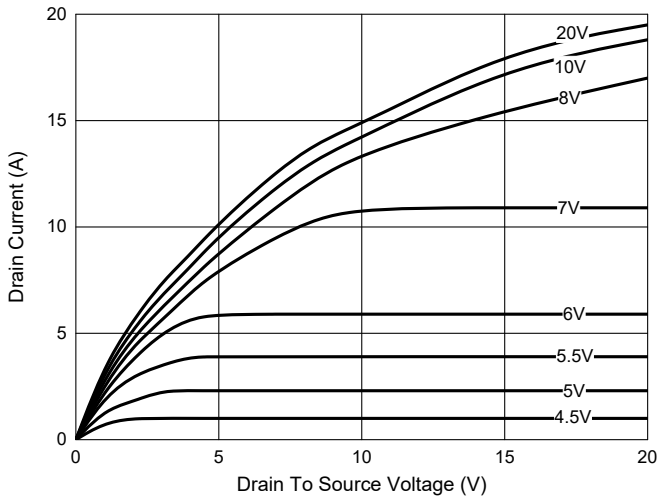


Fig. 2 - Transfer Characteristics

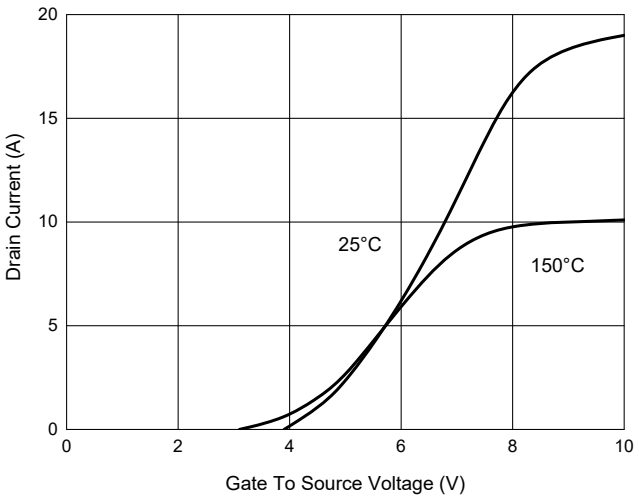


Fig. 3 - $R_{DS(ON)}$—I_D

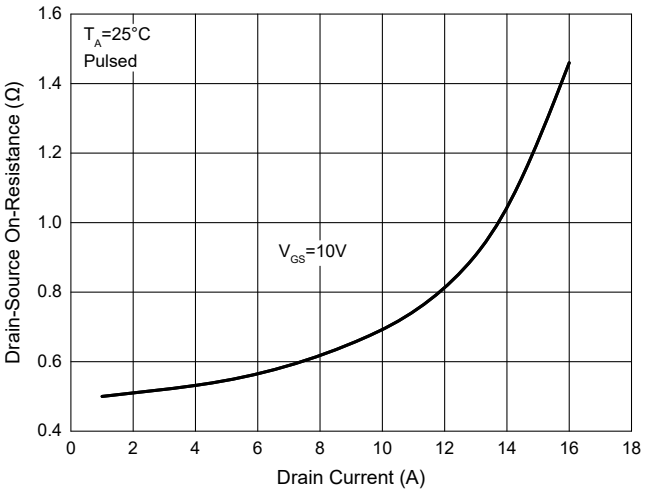


Fig. 4 - Normalized On Resistance Characteristics

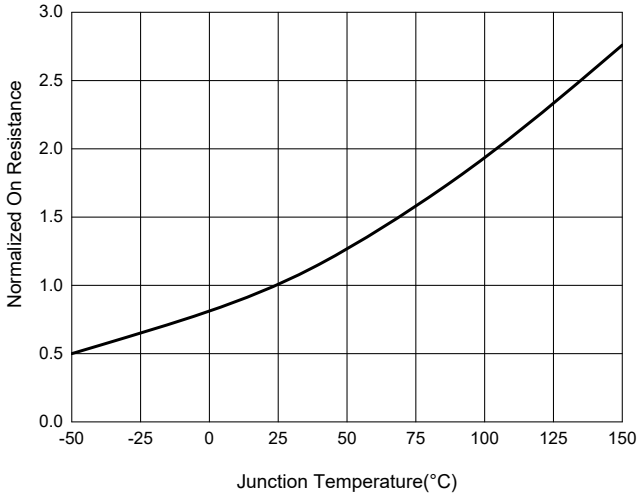


Fig. 5 - Capacitance Characteristics

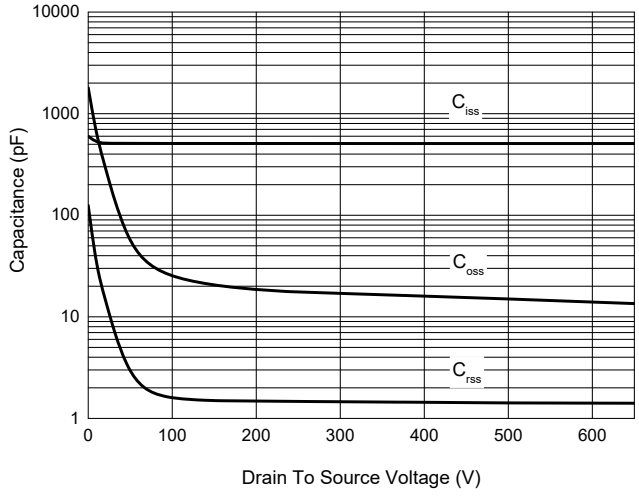
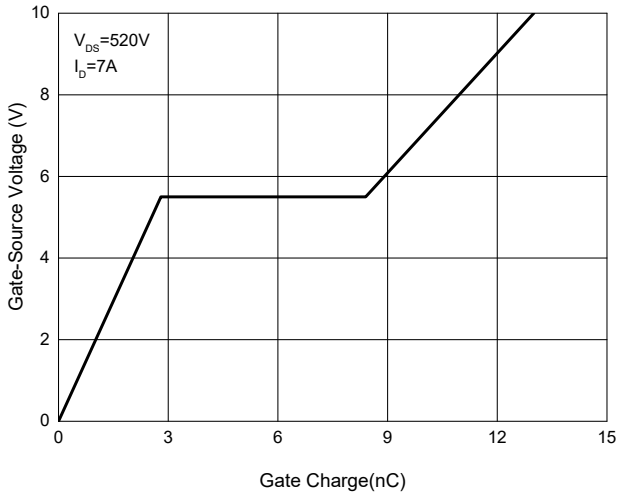


Fig. 6 - Gate Charge



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

Note : Adding "-HF" Suffix for Halogen Free, eg. Part Number-TP-HF